


IRF 520/FI-521/FI
IRF 522/FI-523/FI

S G S-THOMSON

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V _{DSS}	R _{DS(on)}	I _D *
IRF520	100 V	0.27 Ω	9.2 A
IRF520FI	100 V	0.27 Ω	7 A
IRF521	80 V	0.27 Ω	9.2 A
IRF521FI	80 V	0.27 Ω	7 A
IRF522	100 V	0.36 Ω	8 A
IRF522FI	100 V	0.36 Ω	6 A
IRF523	80 V	0.36 Ω	8 A
IRF523FI	80 V	0.36 Ω	6 A

- 80-100 VOLTS - FOR DC/DC CONVERTERS
- HIGH CURRENT
- RATED FOR UNCLAMPED INDUCTIVE SWITCHING (ENERGY TEST) ♦
- ULTRA FAST SWITCHING
- EASY DRIVE- FOR REDUCED COST AND SIZE

INDUSTRIAL APPLICATIONS:

- UNINTERRUPTIBLE POWER SUPPLIES
- MOTOR CONTROLS

N - channel enhancement mode POWER MOS field effect transistors. Easy drive and very fast switching times make these POWER MOS transistors ideal for high speed switching applications. Applications include DC/DC converters, UPS, battery chargers, secondary regulators, servo control, power-audio amplifiers and robotics.

ABSOLUTE MAXIMUM RATINGS

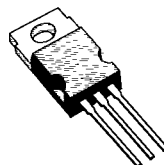
ABSOLUTE MAXIMUM RATINGS		TO-220 ISOWATT220		IRF			
		520 520FI	521 521FI	522 522FI	523 523FI		
V _{DS} *	Drain-source voltage (V _{GS} = 0)	100	80	100	80	V	
V _{DGR} *	Drain-gate voltage (R _{GS} = 20 KΩ)	100	80	100	80	V	
V _{GS}	Gate-source voltage			±20		V	
I _{DM} (•)	Drain current (pulsed)	37	37	32	32	A	
I _D	Drain current (cont.) at T _c = 25°C	520	521	522	523		
I _D	Drain current (cont.) at T _c = 100°C	9.2	9.2	8	8	A	
		6.5	6.5	5.6	5.6	A	
I _D ■	Drain current (cont.) at T _c = 25°C	520FI	521FI	522FI	523FI		
I _D ■	Drain current (cont.) at T _c = 100°C	7	7	6	6	A	
		4	4	3.5	3.5	A	
P _{tot} ■	Total dissipation at T _c < 25°C	TO-220		ISOWATT220		W	
	Derating factor	60		30		W/°C	
T _{stg}	Storage temperature	0.48		0.24		W/°C	
T _j	Max. operating junction temperature	-55 to 150		150		°C	

* T_j = 25°C to 125°C

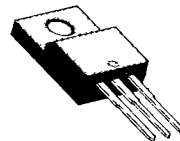
(•) Repetitive Rating: Pulse width limited by max junction temperature.

■ See note on ISOWATT220 on this datasheet.

♦ Introduced in 1988 week 44

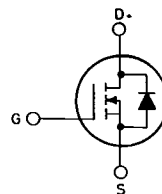


TO-220



ISOWATT220

INTERNAL SCHEMATIC DIAGRAM



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THERMAL DATA*

TO-220 | ISOWATT220

$R_{thj-case}$	Thermal resistance junction-case	max	2.08	4.16	°C/W
R_{tho-s}	Thermal resistance case-sink	typ	0.5		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	max	80		°C/W
T_l	Maximum lead temperature for soldering purpose		300		°C

T-39-11

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
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OFF

$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$ for IRF520/522/520FI/522FI for IRF521/523/521FI/523FI	$V_{GS} = 0$	100 80		V V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$	$T_c = 125^\circ\text{C}$		250 1000	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 500	nA

ON **

$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	$I_D = 250 \mu\text{A}$	2		4	V
$I_{D(on)}$	On-state drain current	$V_{DS} > I_{D(on)} \times R_{DS(on) max}$ for IRF520/521/520FI/521FI for IRF521/523/521FI/523FI	$V_{GS} = 10 \text{ V}$	9.2 8			A A
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$ for IRF520/521/520FI/521FI for IRF522/523/522FI/523FI	$I_D = 5.6 \text{ A}$			0.27 0.36	Ω Ω

ENERGY TEST

I_{UIS}	Unclamped inductive switching current (single pulse)	$V_{DD} = 30 \text{ V}$ starting $T_l = 25^\circ\text{C}$ for IRF520/521/520FI/521FI for IRF522/523/522FI/523FI	$L = 100 \mu\text{H}$	9.2 8			A A
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DYNAMIC

g_{fs}^{**}	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on) max}$ $I_D = 5.6 \text{ A}$		2.7			mho
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}$	$f = 1 \text{ MHz}$			600	pF
C_{oss}	Output capacitance	$V_{GS} = 0$				400	pF
C_{rss}	Reverse transfer capacitance					100	pF

ELECTRICAL CHARACTERISTICS (Continued)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
t_d (on) t_r t_d (off) t_f	Turn-on time Rise time Turn-off delay time Fall time $V_{DD} = 40\text{ V}$ $I_D = 4.0\text{ A}$ $R_i = 50\ \Omega$ (see test circuit)			40 70 100 70	ns ns ns ns
Q_g	Total Gate Charge $V_{GS} = 15\text{ V}$ $V_{DS} = \text{Max Rating} \times 0.8$ (see test circuit) $I_D = 9.2\text{ A}$			15	nC

SWITCHING

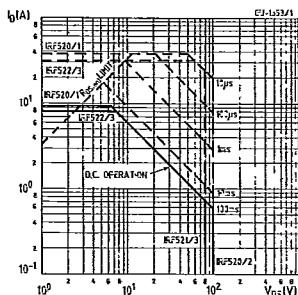
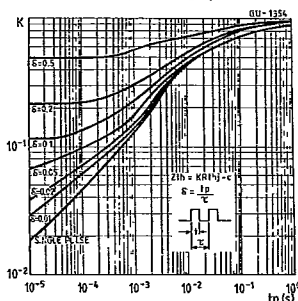
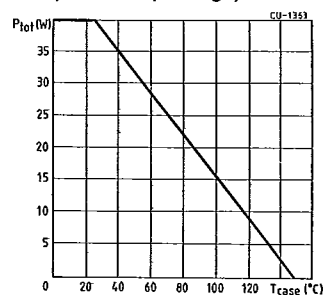
SOURCE DRAIN DIODE

I_{SD} I_{SDM} (*)	Source-drain current Source-drain current (pulsed)			9.2 37	A A
V_{SD}^{**}	Forward on voltage $I_{SD} = 9.2\text{ A}$ $V_{GS} = 0$			2.5	V
t_{rr}	Reverse recovery time $T_j = 150^\circ\text{C}$		280		ns
Q_{rr}	Reverse recovered charge $I_{SD} = 9.2\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$		1.6		μC

** Pulsed: Pulse duration $\leq 300\ \mu\text{s}$, duty cycle $\leq 1.2\%$

(*) Repetitive Rating: Pulse width limited by max junction temperature

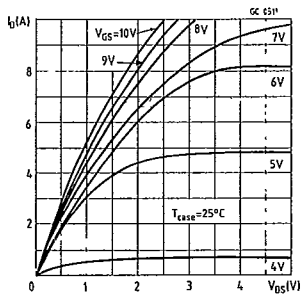
■ See note on ISOWATT220 in this datasheet

Safe operating areas
(standard package)Thermal impedance
(standard package)Derating curve
(standard package)

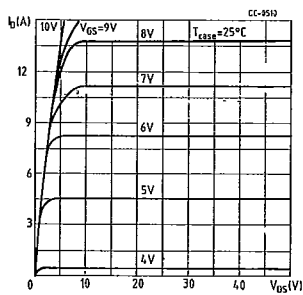
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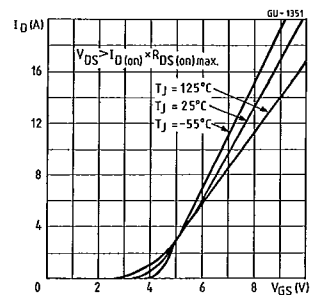
Output characteristics



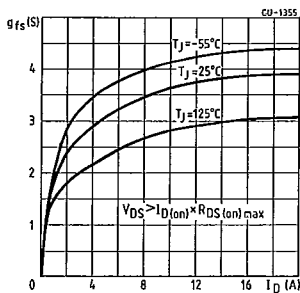
Output characteristics



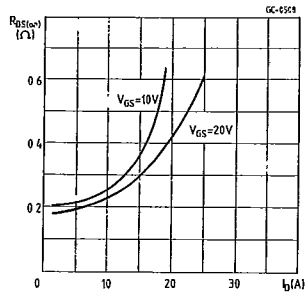
Transfer characteristics



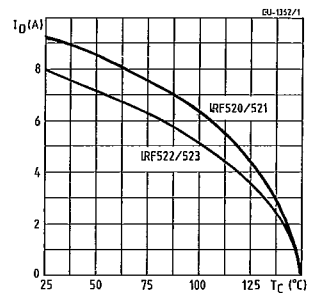
Transconductance



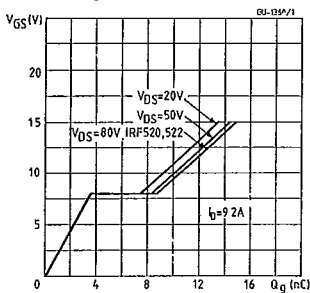
Static drain-source on resistance



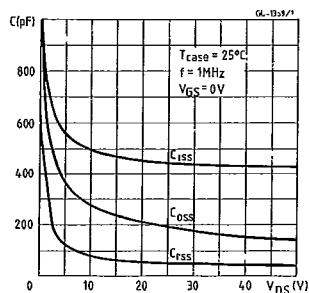
Maximum drain current vs temperature



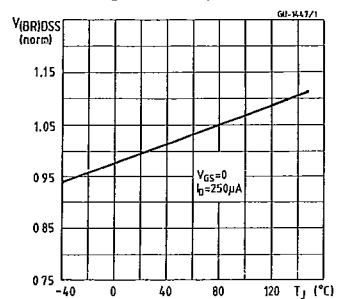
Gate charge vs gate-source voltage



Capacitance variation

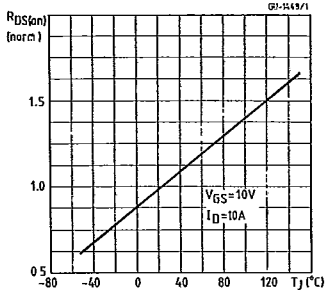
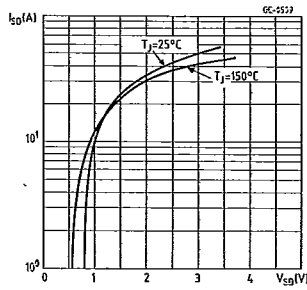


Normalized breakdown voltage vs temperature

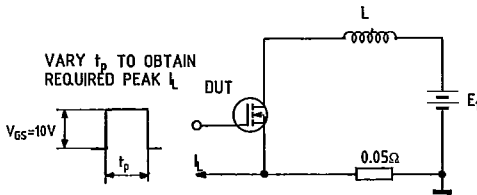


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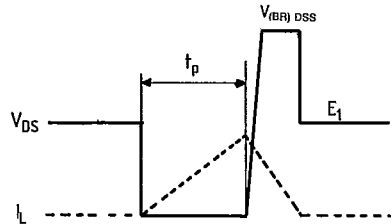
Normalized on resistance
vs temperatureSource-drain diode forward
characteristics

Unclamped inductive test circuit



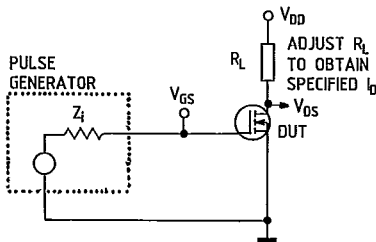
SC-0339

Unclamped inductive waveforms



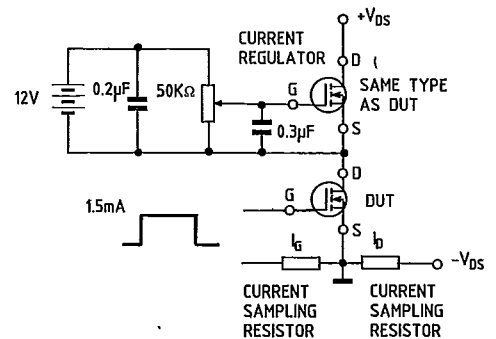
SC-0338

Switching times test circuit



SC-0246

Gate charge test circuit



SC-0244

ISOWATT220 PACKAGE CHARACTERISTICS AND APPLICATION.

ISOWATT220 is fully isolated to 2000V dc. Its thermal impedance, given in the data sheet, is optimised to give efficient thermal conduction together with excellent electrical isolation.

The structure of the case ensures optimum distances between the pins and heatsink. The ISOWATT220 package eliminates the need for external isolation so reducing fixing hardware. Accurate moulding techniques used in manufacture assure consistent heat spreader-to-heatsink capacitance.

ISOWATT220 thermal performance is better than that of the standard part, mounted with a 0.1mm mica washer. The thermally conductive plastic has a higher breakdown rating and is less fragile than mica or plastic sheets. Power derating for ISOWATT220 packages is determined by:

$$P_D = \frac{T_j - T_c}{R_{th}}$$

from this I_{Dmax} for the POWER MOS can be calculated:

$$I_{Dmax} \leq \sqrt{\frac{P_D}{R_{DS(on)} \text{ (at } 150^\circ\text{C)}}}$$

THERMAL IMPEDANCE OF ISOWATT220 PACKAGE

Fig. 1 illustrates the elements contributing to the thermal resistance of transistor heatsink assembly, using ISOWATT220 package.

The total thermal resistance $R_{th \text{ (tot)}}$ is the sum of each of these elements.

The transient thermal impedance, Z_{th} for different pulse durations can be estimated as follows:

1 - for a short duration power pulse less than 1ms;

$$Z_{th} < R_{thJ-C}$$

2 - for an intermediate power pulse of 5ms to 50ms:

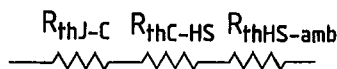
$$Z_{th} = R_{thJ-C}$$

3 - for long power pulses of the order of 500ms or greater:

$$Z_{th} = R_{thJ-C} + R_{thC-HS} + R_{thHS-amb}$$

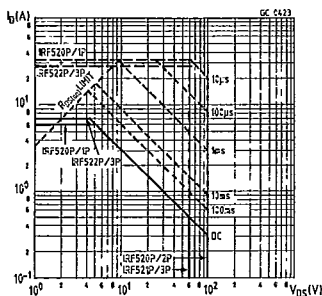
It is often possible to discern these areas on transient thermal impedance curves.

Fig. 1

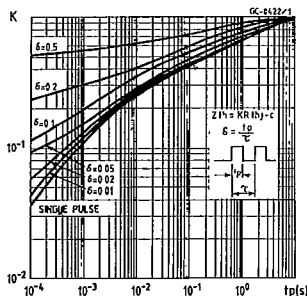


ISOWATT DATA

Safe operating areas



Thermal impedance



Derating curve

